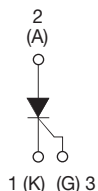
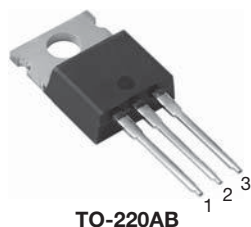


## High Voltage Phase Control Thyristor, 12 A



### FEATURES

- Designed and qualified according to JEDEC-JESD47
- 125 °C max. operating junction temperature
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
**HALOGEN**  
**FREE**  
Available

### APPLICATIONS

- Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

### DESCRIPTION

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

### PRODUCT SUMMARY

|                   |                   |
|-------------------|-------------------|
| Package           | TO-220AB          |
| Diode variation   | Single SCR        |
| $I_{T(AV)}$       | 8 A               |
| $V_{DRM}/V_{RRM}$ | 800 V             |
| $V_{TM}$          | 1.2 V             |
| $I_{GT}$          | 15 mA             |
| $T_J$             | - 40 °C to 125 °C |

### OUTPUT CURRENT IN TYPICAL APPLICATIONS

| APPLICATIONS                                                                     | SINGLE-PHASE BRIDGE | THREE-PHASE BRIDGE | UNITS |
|----------------------------------------------------------------------------------|---------------------|--------------------|-------|
| Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W | 13.5                | 17                 | A     |

### MAJOR RATINGS AND CHARACTERISTICS

| PARAMETER         | TEST CONDITIONS     | VALUES      | UNITS |
|-------------------|---------------------|-------------|-------|
| $I_{T(AV)}$       | Sinusoidal waveform | 8           | A     |
| $I_{T(RMS)}$      |                     | 12.5        |       |
| $V_{DRM}/V_{RRM}$ |                     | 800         | V     |
| $I_{TSM}$         |                     | 110         | A     |
| $V_T$             | 8 A, $T_J = 25$ °C  | 1.2         | V     |
| $dV/dt$           |                     | 150         | V/μs  |
| $dI/dt$           |                     | 100         | A/μs  |
| $T_J$             | Range               | - 40 to 125 | °C    |

### VOLTAGE RATINGS

| PART NUMBER                  | $V_{RRM}$ , MAXIMUM PEAK VOLTAGE<br>V | $V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE<br>V | $I_{RRM}/I_{DRM}$ AT 125 °C<br>mA |
|------------------------------|---------------------------------------|----------------------------------------------|-----------------------------------|
| VS-12TTS08PbF, VS-12TTS08-M3 | 800                                   | 800                                          | 1.0                               |

**ABSOLUTE MAXIMUM RATINGS**

| PARAMETER                                             | SYMBOL          | TEST CONDITIONS                                                                                      | VALUES | UNITS                       |
|-------------------------------------------------------|-----------------|------------------------------------------------------------------------------------------------------|--------|-----------------------------|
| Maximum average on-state current                      | $I_{T(AV)}$     | $T_C = 108\text{ }^{\circ}\text{C}$ , $180^{\circ}$ conduction, half sine wave                       | 8      | A                           |
| Maximum RMS on-state current                          | $I_{T(RMS)}$    |                                                                                                      | 12.5   |                             |
| Maximum peak, one-cycle, non-repetitive surge current | $I_{TSM}$       | 10 ms sine pulse, rated $V_{RRM}$ applied, $T_J = 125\text{ }^{\circ}\text{C}$                       | 95     |                             |
|                                                       |                 | 10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$                          | 110    |                             |
| Maximum $I^2t$ for fusing                             | $I^2t$          | 10 ms sine pulse, rated $V_{RRM}$ applied, $T_J = 125\text{ }^{\circ}\text{C}$                       | 45     | $\text{A}^2\text{s}$        |
|                                                       |                 | 10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$                          | 64     |                             |
| Maximum $I^2\sqrt{t}$ for fusing                      | $I^2\sqrt{t}$   | $t = 0.1\text{ ms to }10\text{ ms}$ , no voltage reapplied, $T_J = 125\text{ }^{\circ}\text{C}$      | 640    | $\text{A}^2\sqrt{\text{s}}$ |
| Maximum on-state voltage drop                         | $V_{TM}$        | 8 A, $T_J = 25\text{ }^{\circ}\text{C}$                                                              | 1.2    | V                           |
| On-state slope resistance                             | $r_t$           | $T_J = 125\text{ }^{\circ}\text{C}$                                                                  | 16.2   | $\text{m}\Omega$            |
| Threshold voltage                                     | $V_{T(TO)}$     |                                                                                                      | 0.87   | V                           |
| Maximum reverse and direct leakage current            | $I_{RM}/I_{DM}$ | $T_J = 25\text{ }^{\circ}\text{C}$                                                                   | 0.05   | mA                          |
|                                                       |                 | $T_J = 125\text{ }^{\circ}\text{C}$                                                                  | 1.0    |                             |
| Typical holding current                               | $I_H$           | Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$ , $T_J = 25\text{ }^{\circ}\text{C}$  | 30     |                             |
| Maximum latching current                              | $I_L$           | Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$                               | 50     |                             |
| Maximum rate of rise of off-state voltage             | $dV/dt$         | $T_J = T_J\text{ max.}$ , linear to $80\text{ }^{\circ}\text{C}$ , $V_{DRM} = R_g - k = \text{Open}$ | 150    | $\text{V}/\mu\text{s}$      |
| Maximum rate of rise of turned-on current             | $dI/dt$         |                                                                                                      | 100    | $\text{A}/\mu\text{s}$      |

**TRIGGERING**

| PARAMETER                                   | SYMBOL      | TEST CONDITIONS                                                         | VALUES | UNITS |
|---------------------------------------------|-------------|-------------------------------------------------------------------------|--------|-------|
| Maximum peak gate power                     | $P_{GM}$    |                                                                         | 8.0    | W     |
| Maximum average gate power                  | $P_{G(AV)}$ |                                                                         | 2.0    |       |
| Maximum peak positive gate current          | $+I_{GM}$   |                                                                         | 1.5    | A     |
| Maximum peak negative gate voltage          | $-V_{GM}$   |                                                                         | 10     | V     |
| Maximum required DC gate current to trigger | $I_{GT}$    | Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$ | 20     | mA    |
|                                             |             | Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$  | 15     |       |
|                                             |             | Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$ | 10     |       |
| Maximum required DC gate voltage to trigger | $V_{GT}$    | Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$ | 1.2    | V     |
|                                             |             | Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$  | 1      |       |
|                                             |             | Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$ | 0.7    |       |
| Maximum DC gate voltage not to trigger      | $V_{GD}$    | $T_J = 125\text{ }^{\circ}\text{C}$ , $V_{DRM} = \text{Rated value}$    | 0.2    | mA    |
| Maximum DC gate current not to trigger      | $I_{GD}$    |                                                                         | 0.1    |       |

**SWITCHING**

| PARAMETER                     | SYMBOL   | TEST CONDITIONS                     | VALUES | UNITS         |
|-------------------------------|----------|-------------------------------------|--------|---------------|
| Typical turn-on time          | $t_{gt}$ | $T_J = 25\text{ }^{\circ}\text{C}$  | 0.8    | $\mu\text{s}$ |
| Typical reverse recovery time | $t_{rr}$ | $T_J = 125\text{ }^{\circ}\text{C}$ | 3      |               |
| Typical turn-off time         | $t_q$    |                                     | 100    |               |



| THERMAL AND MECHANICAL SPECIFICATIONS           |                                   |                                      |             |                        |
|-------------------------------------------------|-----------------------------------|--------------------------------------|-------------|------------------------|
| PARAMETER                                       | SYMBOL                            | TEST CONDITIONS                      | VALUES      | UNITS                  |
| Maximum junction and storage temperature range  | T <sub>J</sub> , T <sub>Stg</sub> |                                      | - 40 to 125 | °C                     |
| Maximum thermal resistance, junction to case    | R <sub>thJC</sub>                 | DC operation                         | 1.5         | °C/W                   |
| Maximum thermal resistance, junction to ambient | R <sub>thJA</sub>                 |                                      | 62          |                        |
| Typical thermal resistance, case to heatsink    | R <sub>thCS</sub>                 | Mounting surface, smooth and greased | 0.5         |                        |
| Approximate weight                              |                                   |                                      | 2           | g                      |
|                                                 |                                   |                                      | 0.07        | oz.                    |
| Mounting torque                                 | minimum                           |                                      | 6 (5)       | kgf · cm<br>(lbf · in) |
|                                                 | maximum                           |                                      | 12 (10)     |                        |
| Marking device                                  |                                   | Case style TO-220AB                  | 12TTS08     |                        |

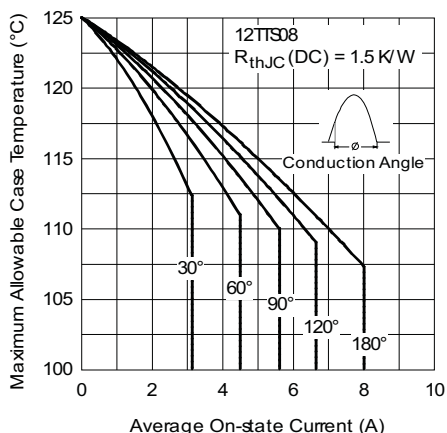


Fig. 1 - Current Ratings Characteristics

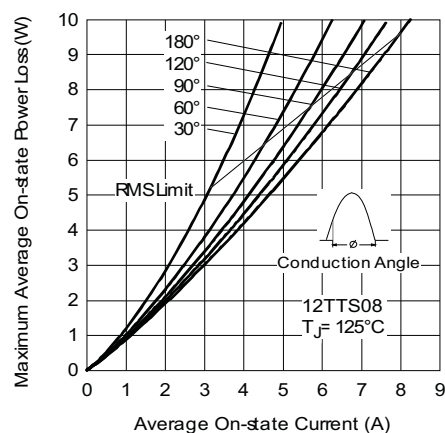


Fig. 3 - On-State Power Loss Characteristics

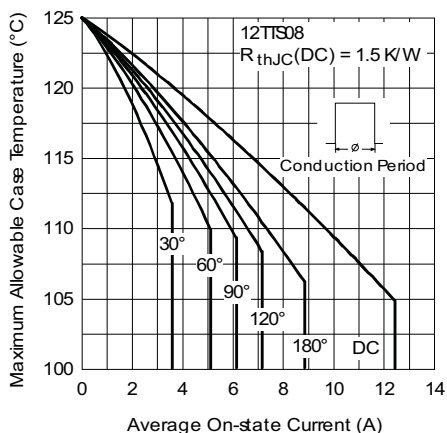


Fig. 2 - Current Ratings Characteristics

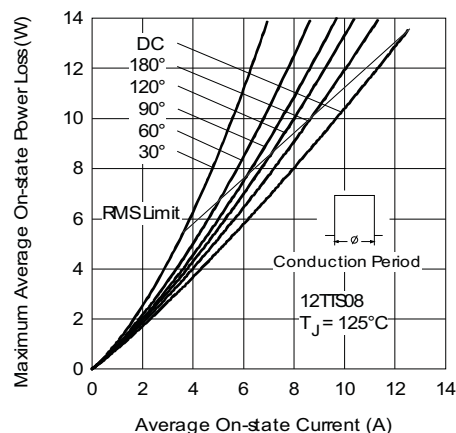


Fig. 4 - On-State Power Loss Characteristics

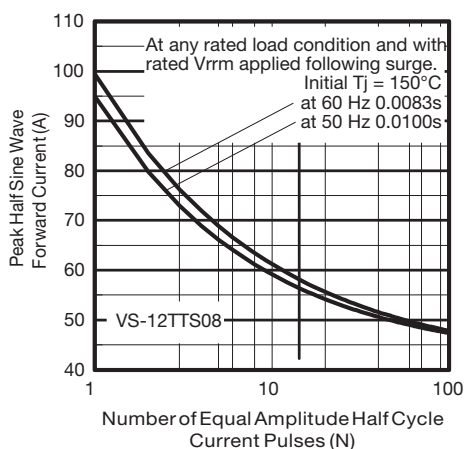


Fig. 5 - Maximum Non-Repetitive Surge Current

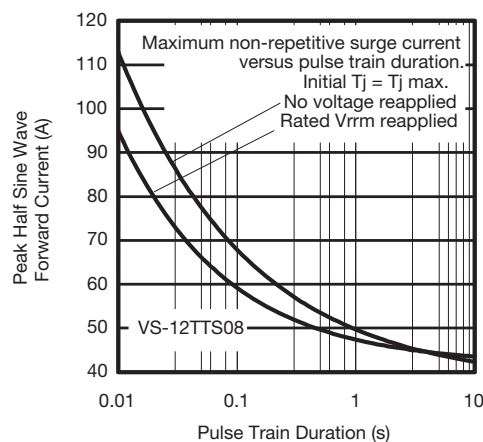


Fig. 6 - Maximum Non-Repetitive Surge Current

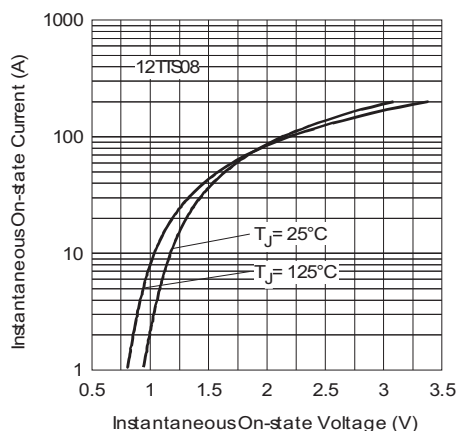
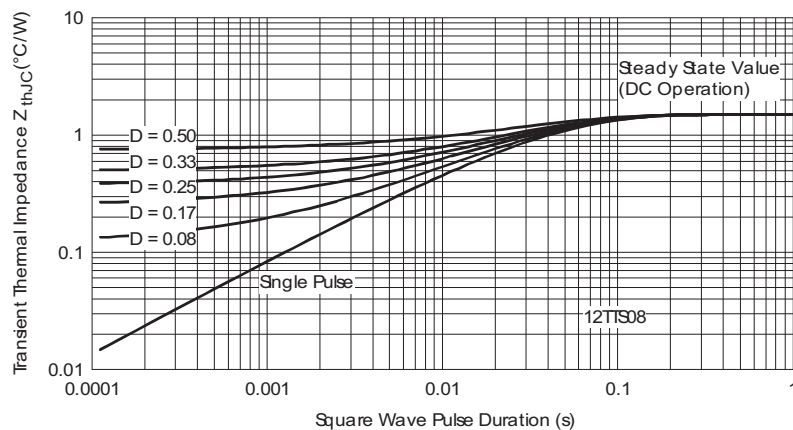


Fig. 7 - On-State Voltage Drop Characteristics


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

**ORDERING INFORMATION TABLE**

|             |            |           |          |          |          |           |            |
|-------------|------------|-----------|----------|----------|----------|-----------|------------|
| Device code | <b>VS-</b> | <b>12</b> | <b>T</b> | <b>T</b> | <b>S</b> | <b>08</b> | <b>PbF</b> |
|             | 1          | 2         | 3        | 4        | 5        | 6         | 7          |

- 1** - Vishay Semiconductors product
- 2** - Current ratings (12 = 12.5 A)
- 3** - Circuit configuration:  
T = Single thyristor
- 4** - Package:  
T = TO-220
- 5** - Type of silicon  
S = Standard recovery rectifier
- 6** - Voltage rating (08 = 800 V)
- 7** - Environmental digit:  
PbF = Lead (Pb)-free and RoHS compliant  
-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

| <b>ORDERING INFORMATION</b> (Example) |                         |                               |                              |
|---------------------------------------|-------------------------|-------------------------------|------------------------------|
| <b>PREFERRED P/N</b>                  | <b>QUANTITY PER T/R</b> | <b>MINIMUM ORDER QUANTITY</b> | <b>PACKAGING DESCRIPTION</b> |
| VS-12TTS08PbF                         | 50                      | 1000                          | Antistatic plastic tubes     |
| VS-12TTS08-M3                         | 50                      | 1000                          | Antistatic plastic tubes     |

| <b>LINKS TO RELATED DOCUMENTS</b> |              |                                                                        |
|-----------------------------------|--------------|------------------------------------------------------------------------|
| Dimensions                        |              | <a href="http://www.vishay.com/doc?95222">www.vishay.com/doc?95222</a> |
| Part marking information          | TO-220AB PbF | <a href="http://www.vishay.com/doc?95225">www.vishay.com/doc?95225</a> |
|                                   | TO-220AB -M3 | <a href="http://www.vishay.com/doc?95028">www.vishay.com/doc?95028</a> |



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- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
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